



GPA/1765

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Jason M. Benz

Serial No.: 09/695,028

Group Art Unit: 1765

Filed: October 24, 2000

Examiner: Alanko, Anita K.

For: METHOD FOR THIN FILM LASER REFLECTANCE CORRELATION FOR
SUBSTRATE ETCH ENDPOINT

EXCESS CLAIM FEE PAYMENT LETTER

Sir:

Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

	<u>AFTER AMENDMENT</u>	<u>PREV. PAID FOR</u>	<u>EXTRA CLAIMS PRESENT</u>	<u>RATE</u>	<u>FEES DUE</u>
Total Claims	33	-	= 3	x \$18.00	\$ 54.00
Indep. Claims	3	-	= 0	x \$84.00	\$.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$ 54.00

Please charge Assignee's Deposit Account No. 09-0456 in the amount of \$ 54.00 to cover the excess claim fees. A duplicate copy of this sheet is enclosed. The Commissioner is authorized to charge any deficiencies in fees and credit any overpayment of fees to Assignee's Deposit Account No. 09-0456.

Respectfully Submitted,

 #46,060

Sean M. McGinn
Reg. No. 34,386

Date: 10/21/02

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re Application of

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MA
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Honorable Commissioner of Patents
Washington, D.C. 20231

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AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated July 8, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

10/10/2002 EHAILE1 00000028 090456 09695028
01 FC:103 54.00 CH

Please amend the claims as follows:

B1 1. (Amended) A method of etching a substrate, comprising:
2 measuring a reflectance signal from a reflective material deposited on said substrate as
3 the substrate is being etched;
4 correlating the substrate etch rate to the reflectance signal from the reflective material;
5 and
6 using the etch relation between the substrate and the reflective material to determine
7 the etch target,
8 wherein said reflective material is isolated from an etching process.

B2D3 1. (Amended) The method of claim 1, wherein said reflective material comprises metal
having a metal oxide thereon, and said substrate etch also etches said metal oxide on said